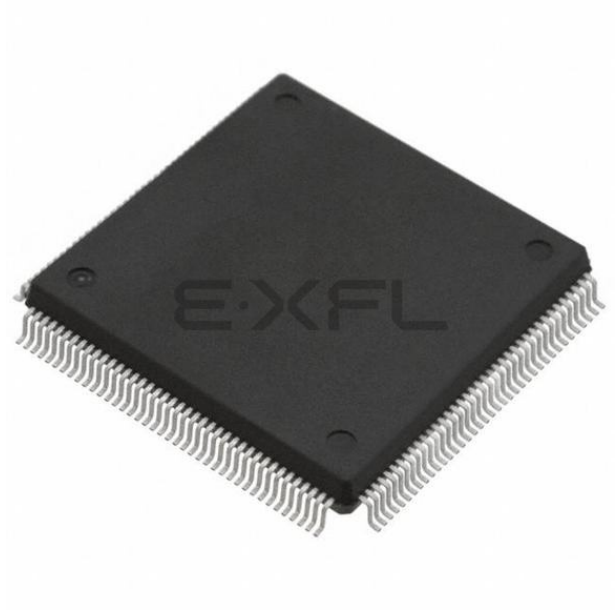

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	Coldfire V2
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	EBI/EMI, Ethernet, I²C, SPI, UART/USART
Peripherals	DMA, WDT
Number of I/O	39
Program Memory Size	-
Program Memory Type	ROMless
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.4V ~ 1.6V
Data Converters	-
Oscillator Type	External
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	160-BQFP
Supplier Device Package	160-QFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcf5270cab100

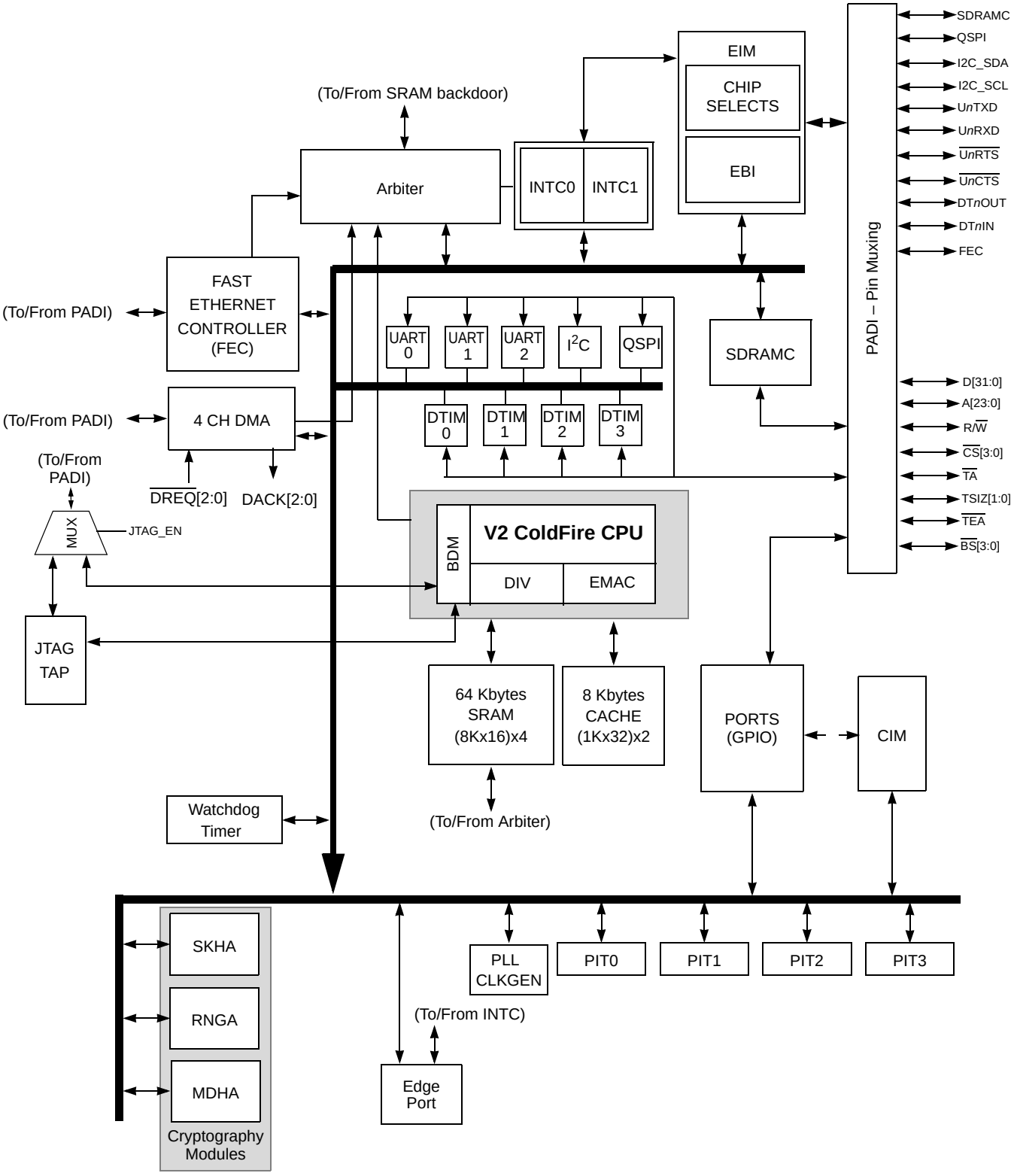
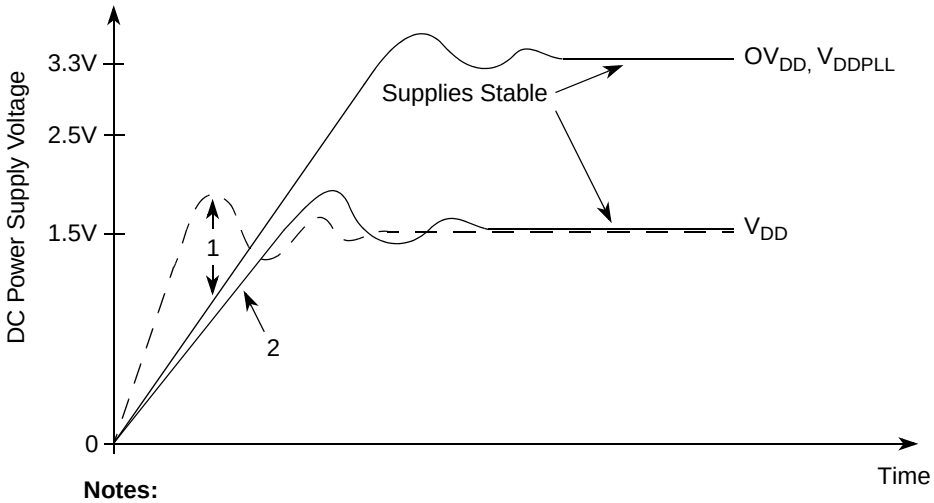


Figure 1. MCF5271 Block Diagram

5.2.1 Supply Voltage Sequencing and Separation Cautions

Figure 2 shows situations in sequencing the I/O V_{DD} (OV_{DD}), PLL V_{DD} (V_{DDPLL}), and Core V_{DD} (V_{DD}). OV_{DD} is specified relative to V_{DD}.



Notes:
1. VDD should not exceed OVDD or VDDPLL by more than 0.4 V at any time, including power-up.
2. Recommended that VDD should track OVDD/VDDPLL up to 0.9 V, then separate for completion of ramps.
3. Input voltage must not be greater than the supply voltage (OVDD, VDD, or VDDPLL) by more than 0.5 V at any time, including during power-up.
4. Use 1 ms or slower rise time for all supplies.

Figure 2. Supply Voltage Sequencing and Separation Cautions

5.2.1.1 Power Up Sequence

If OV_{DD} is powered up with V_{DD} at 0 V, then the sense circuits in the I/O pads cause all pad output drivers connected to the OV_{DD} to be in a high impedance state. There is no limit on how long after OV_{DD} powers up before V_{DD} must power up. V_{DD} should not lead the OV_{DD} or V_{DDPLL} by more than 0.4 V during power ramp-up, or there will be high current in the internal ESD protection diodes. The rise times on the power supplies should be slower than 1 μs to avoid turning on the internal ESD protection clamp diodes.

The recommended power up sequence is as follows:

1. Use 1 ms or slower rise time for all supplies.
2. V_{DD} and OV_{DD}/V_{DDPLL} should track up to 0.9 V, then separate for the completion of ramps with OV_{DD} going to the higher external voltages. One way to accomplish this is to use a low drop-out voltage regulator.

5.2.1.2 Power Down Sequence

If V_{DD} is powered down first, then sense circuits in the I/O pads cause all output drivers to be in a high impedance state. There is no limit on how long after V_{DD} powers down before OV_{DD}/V_{DDPLL} must power down. V_{DD} should not lag OV_{DD} or V_{DDPLL} going low by more than 0.4 V during power down or there

Table 3. Synchronous DRAM Signal Connections

Signal	Description
$\overline{\text{SD\_SRAS}}$	Synchronous row address strobe. Indicates a valid SDRAM row address is present and can be latched by the SDRAM. $\overline{\text{SD\_SRAS}}$ should be connected to the corresponding SDRAM $\overline{\text{SD\_SRAS}}$. Do not confuse $\overline{\text{SD\_SRAS}}$ with the DRAM controller's $\overline{\text{SD\_CS}}$[1:0], which should not be interfaced to the SDRAM $\overline{\text{SD\_SRAS}}$ signals.
$\overline{\text{SD\_SCAS}}$	Synchronous column address strobe. Indicates a valid column address is present and can be latched by the SDRAM. $\overline{\text{SD\_SCAS}}$ should be connected to the corresponding signal labeled $\overline{\text{SD\_SCAS}}$ on the SDRAM.
$\overline{\text{DRAMW}}$	DRAM read/write. Asserted for write operations and negated for read operations.
$\overline{\text{SD\_CS}}$[1:0]	Row address strobe. Select each memory block of SDRAMs connected to the MCF5271. One $\overline{\text{SD\_CS}}$ signal selects one SDRAM block and connects to the corresponding $\overline{\text{CS}}$ signals.
SD_CKE	Synchronous DRAM clock enable. Connected directly to the CKE (clock enable) signal of SDRAMs. Enables and disables the clock internal to SDRAM. When CKE is low, memory can enter a power-down mode where operations are suspended or they can enter self-refresh mode. SD_CKE functionality is controlled by DCR[COC]. For designs using external multiplexing, setting COC allows SD_CKE to provide command-bit functionality.
$\overline{\text{BS}}$[3:0]	Column address strobe. For synchronous operation, $\overline{\text{BS}}$[3:0] function as byte enables to the SDRAMs. They connect to the DQM signals (or mask qualifiers) of the SDRAMs.
CLKOUT	Bus clock output. Connects to the CLK input of SDRAMs.

5.7.1.2 Address Multiplexing

See the SDRAM controller module chapter in the *MCF5271 Reference Manual* for details on address multiplexing.

5.7.2 Ethernet PHY Transceiver Connection

The FEC supports both an MII interface for 10/100 Mbps Ethernet and a seven-wire serial interface for 10 Mbps Ethernet. The interface mode is selected by R_CNTRL[MII_MODE]. In MII mode, the 802.3 standard defines and the FEC module supports 18 signals. These are shown in Table 4.

Table 4. MII Mode

Signal Description	MCF5271 Pin
Transmit clock	ETXCLK
Transmit enable	ETXEN
Transmit data	ETXD[3:0]
Transmit error	ETXER
Collision	ECOL
Carrier sense	ECRS
Receive clock	ERXCLK
Receive enable	ERXDV
Receive data	ERXD[3:0]

Table 4. MII Mode (continued)

Signal Description	MCF5271 Pin
Receive error	ERXER
Management channel clock	EMDC
Management channel serial data	EMDIO

The serial mode interface operates in what is generally referred to as AMD mode. The MCF5271 configuration for seven-wire serial mode connections to the external transceiver are shown in Table 5.

Table 5. Seven-Wire Mode Configuration

Signal Description	MCF5271 Pin
Transmit clock	ETXCLK
Transmit enable	ETXEN
Transmit data	ETXD[0]
Collision	ECOL
Receive clock	ERXCLK
Receive enable	ERXDV
Receive data	ERXD[0]
Unused, configure as PB14	ERXER
Unused input, tie to ground	ECRS
Unused, configure as PB[13:11]	ERXD[3:1]
Unused output, ignore	ETXER
Unused, configure as PB[10:8]	ETXD[3:1]
Unused, configure as PB15	EMDC
Input after reset, connect to ground	EMDIO

Refer to the M5271EVB evaluation board user's manual for an example of how to connect an external PHY. Schematics for this board are accessible at the MCF5271 site by navigating to: http://www.freescale.com/coldfire.

5.7.3 BDM

Use the BDM interface as shown in the M5271EVB evaluation board user's manual. The schematics for this board are accessible at the Freescale website at: http://www.freescale.com/coldfire.

6 Mechanicals/Pinouts and Part Numbers

This section contains drawings showing the pinout and the packaging and mechanical characteristics of the MCF5271 devices. See Table 4 for a list the signal names and pin locations for each device.

6.1 Pinout—196 MAPBGA

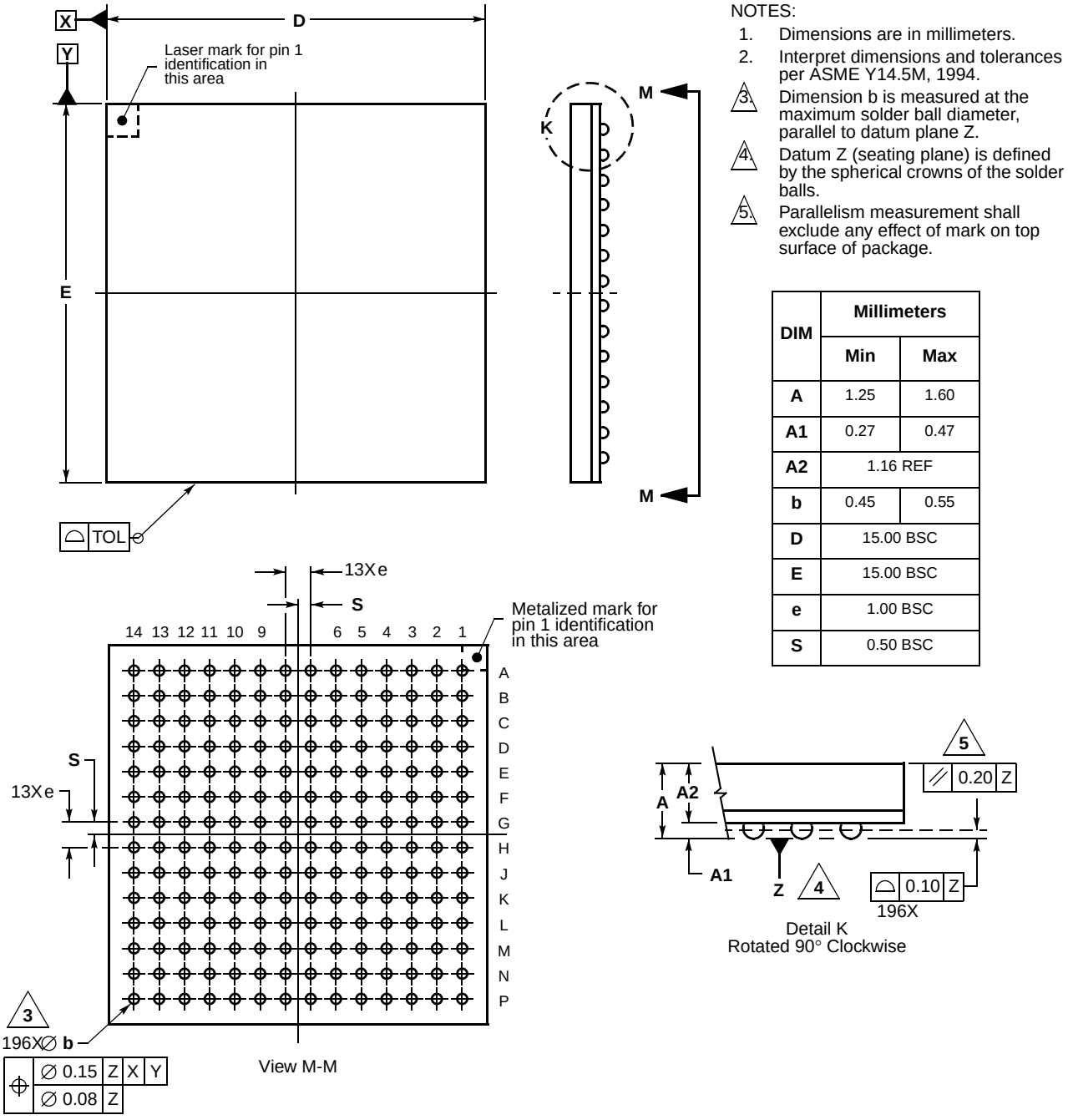
The following figure shows a pinout of the MCF5270/71CVMxxx package.

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	
A	VSS	ETXCLK	ETXD3	ETXD2	QSPI_DOUT	QSPI_CS0	U2RXD	U2TXD	$\overline{CS3}$	$\overline{CS6}$	$\overline{CS4}$	A20	A17	VSS	A
B	ERXD0	ERXER	ETXER	ETXD0	QSPI_DIN	$\overline{BS3}$	QSPI_CS1	U1CTS	$\overline{CS7}$	$\overline{CS1}$	A23	A19	A16	A15	B
C	ERXD2	ERXD1	ETXEN	ETXD1	QSCK	$\overline{BS2}$	$\overline{BS0}$	RTS1	$\overline{CS2}$	$\overline{CS5}$	A22	A18	A14	A13	C
D	ERXCLK	ERXDV	ERXD3	EMDC	EMDIO	Core VDD_4	$\overline{BS1}$	U1RXD1	U1TXD	$\overline{CS0}$	A21	A12	A11	A10	D
E	ECRS	ECOL	NC	TIN0	VDD	VSS	VDD	SD_CKE	VSS	VDD	A9	A8	A7	A6	E
F	U0TXD	U0RXD	U0CTS	DTOUT0	TEST	VSS	VDD	VSS	VDD	VSS	Core VDD_3	A5	A4	A3	F
G	D31	D30	U0RTS	Core VDD_1	CLK MOD1	VDD	VSS	VDD	VSS	NC	A2	A1	A0	DTOUT3	G
H	D29	D28	D27	D26	CLK MOD0	VSS	VDD	VDD	VDD	NC	$\overline{TA}$	$\overline{TIP}$	$\overline{TS}$	DTIN3	H
J	D25	D24	D23	D22	VSS	VDD	VSS	VDD	VSS	VDD	I2C_SCL	I2C_SDA	R/$\overline{W}$	$\overline{TEA}$	J
K	D21	D20	D19	D18	VDD	VDD	VSS	VDD	JTAG_EN	$\overline{RCON}$	$\overline{SD\_RAS}$	$\overline{SD\_CAS}$	$\overline{SD\_WE}$	CLKOUT	K
L	D17	D16	D10	Core VDD_2	D3	DTIN1	$\overline{IRQ5}$	$\overline{IRQ1}$	DTOUT2	PST0	DDATA0	$\overline{SD\_CS1}$	$\overline{SD\_CS0}$	VSSPLL	L
M	D15	D13	D9	D6	D2	DTOUT1	$\overline{IRQ6}$	$\overline{IRQ2}$	DTIN2	TDI/DSI	PST3	DDATA3	VDDPLL	EXTAL	M
N	D14	D12	D8	D5	D1	$\overline{OE}$	$\overline{IRQ7}$	$\overline{IRQ3}$	$\overline{TRST}$/DSCLK	TDO/DSO	PST2	DDATA2	$\overline{RESET}$	XTAL	N
P	VSS	D11	D7	D4	D0	TSIZ1	TSIZ0	$\overline{IRQ4}$	TCLK/PSTCLK	$\overline{TMS}$/$\overline{BKPT}$	PST1	DDATA1	$\overline{RSTOUT}$	VSS	P
	1	2	3	4	5	6	7	8	9	10	11	12	13	14	

Figure 3. MCF5270/71CVMxxx Pinout (196 MAPBGA)

6.2 Package Dimensions—196 MAPBGA

Figure 4 shows MCF5270/71CVMxxx package dimensions.



NOTES:
1. Dimensions are in millimeters.
2. Interpret dimensions and tolerances per ASME Y14.5M, 1994.
3. Dimension b is measured at the maximum solder ball diameter, parallel to datum plane Z.
4. Datum Z (seating plane) is defined by the spherical crowns of the solder balls.
5. Parallelism measurement shall exclude any effect of mark on top surface of package.

DIM	Millimeters	
	Min	Max
A	1.25	1.60
A1	0.27	0.47
A2	1.16 REF	
b	0.45	0.55
D	15.00 BSC	
E	15.00 BSC	
e	1.00 BSC	
S	0.50 BSC	

Figure 4. 196 MAPBGA Package Dimensions (Case No. 1128A-01)

6.5 Ordering Information

Table 6. Orderable Part Numbers

Freescale Part Number	Description	Package	Speed	Lead-Free?	Temperature
MCF5270AB100	MCF5270 RISC Microprocessor	160 QFP	100MHz	Yes	0° to +70° C
MCF5270CAB100	MCF5270 RISC Microprocessor	160 QFP	100MHz	Yes	-40° to +85° C
MCF5270VM100	MCF5270 RISC Microprocessor	196 MAPBGA	100MHz	Yes	0° to +70° C
MCF5270CVM150	MCF5270 RISC Microprocessor	196 MAPBGA	150MHz	Yes	-40° to +85° C
MCF5271CAB100	MCF5271 RISC Microprocessor	160 QFP	100MHz	Yes	-40° to +85° C
MCF5271CVM100	MCF5271 RISC Microprocessor	196 MAPBGA	100MHz	Yes	-40° to +85° C
MCF5271CVM150	MCF5271 RISC Microprocessor	196 MAPBGA	150MHz	Yes	-40° to +85° C

7 Electrical Characteristics

This chapter contains electrical specification tables and reference timing diagrams for the MCF5271 microcontroller unit. This section contains detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications of MCF5271.

NOTE

The parameters specified in this processor document supersede any values found in the module specifications.

7.1 Maximum Ratings

Table 7. Absolute Maximum Ratings[1, 2]

Rating	Symbol	Value	Unit
Core Supply Voltage	V_{DD}	– 0.5 to +2.0	V
Pad Supply Voltage	OV_{DD}	– 0.3 to +4.0	V
PLL Supply Voltage	V_{DDPLL}	– 0.3 to +4.0	V
Digital Input Voltage [3]	V_{IN}	– 0.3 to + 4.0	V
Instantaneous Maximum Current Single pin limit (applies to all pins) [3,4,5]	I_D	25	mA
Operating Temperature Range (Packaged)	T_A (T_L - T_H)	– 40 to 85	°C
Storage Temperature Range	T_{stg}	– 65 to 150	°C

1 Functional operating conditions are given in DC Electrical Specifications. Absolute Maximum Ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Continued operation at these levels may affect device reliability or cause permanent damage to the device.

Table 9. DC Electrical Specifications[1] (continued)

Characteristic	Symbol	Min	Typical	Max	Unit
Load Capacitance[4] Low drive strength High drive strength	C_L		— —	25 50	pF pF
Core Operating Supply Current [5] Master Mode	I_{DD}	—	135	150	mA
Pad Operating Supply Current Master Mode Low Power Modes	OI_{DD}	— —	100 TBD	— —	mA µA
DC Injection Current [3, 6, 7, 8] $V_{NEGCLAMP}$ =V_{SS}– 0.3 V, $V_{POSCLAMP}$ = V_{DD} + 0.3 Single Pin Limit Total processor Limit, Includes sum of all stressed pins	I_{IC}	 –1.0 –10		 1.0 10	 mA mA

1 Refer to Table 10 for additional PLL specifications.
2 Refer to the MCF5271 signals section for pins having weak internal pull-up devices.
3 This parameter is characterized before qualification rather than 100% tested.
4 pF load ratings are based on DC loading and are provided as an indication of driver strength. High speed interfaces require transmission line analysis to determine proper drive strength and termination. See High Speed Signal Propagation: Advanced Black Magic by Howard W. Johnson for design guidelines.
5 Current measured at maximum system clock frequency, all modules active, and default drive strength with matching load.
6 All functional non-supply pins are internally clamped to V_{SS} and their respective V_{DD}.
7 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.
8 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{in} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Insure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the processor is not consuming power. Examples are: if no system clock is present, or if clock rate is very low which would reduce overall power consumption. Also, at power-up, system clock is not present during the power-up sequence until the PLL has attained lock.

7.4 Oscillator and PLLMRFM Electrical Characteristics

Table 10. HiP7 PLLMRFM Electrical Specifications[1]

Num	Characteristic	Symbol	Min. Value	Max. Value	Unit
1	PLL Reference Frequency Range Crystal reference External reference 1:1 mode (NOTE: $f_{sys/2} = 2 \times f_{ref\_1:1}$)	 $f_{ref\_crystal}$ f_{ref_ext} $f_{ref\_1:1}$	 8 8 24	 25 25 75	MHz
2	Core frequency CLKOUT Frequency [2] External reference On-Chip PLL Frequency	f_{sys} $f_{sys/2}$	 0 $f_{ref} \div 32$	150 75 75	MHz MHz MHz
3	Loss of Reference Frequency [3, 5]	f_{LOR}	100	1000	kHz
4	Self Clocked Mode Frequency [4, 5]	f_{SCM}	10.25	15.25	MHz
5	Crystal Start-up Time [5, 6]	t_{cst}	—	10	ms

Table 10. HiP7 PLLMRFM Electrical Specifications[1] (continued)

Num	Characteristic	Symbol	Min. Value	Max. Value	Unit
6	XTAL Load Capacitance[5]		5	30	pF
7	PLL Lock Time [5, 7,13]	t_{lpll}	—	750	µs
8	Power-up To Lock Time [5, 6,8] With Crystal Reference (includes 5 time) Without Crystal Reference[9]	t_{lplk}	 — —	 11 750	 ms µs
9	1:1 Mode Clock Skew (between CLKOUT and EXTAL) [10]	t_{skew}	–1	1	ns
10	Duty Cycle of reference [5]	t_{dc}	40	60	%
11	Frequency un-LOCK Range	f_{UL}	–3.8	4.1	% $f_{sys/2}$
12	Frequency LOCK Range	f_{LCK}	–1.7	2.0	% $f_{sys/2}$
13	CLKOUT Period Jitter, [5, 6, 8,11, 12] Measured at $f_{sys/2}$ Max Peak-to-peak Jitter (Clock edge to clock edge) Long Term Jitter (Averaged over 2 ms interval)	C_{jitter}	 — —	 5.0 .01	% $f_{sys/2}$
14	Frequency Modulation Range Limit[13,14] ($f_{sys/2}$ Max must not be exceeded)	C_{mod}	0.8	2.2	%$f_{sys/2}$
15	ICO Frequency. $f_{ico} = f_{ref} \times 2 \times (MFD+2)$ [15]	f_{ico}	48	150	MHz

1 All values given are initial design targets and subject to change.
2 All internal registers retain data at 0 Hz.
3 “Loss of Reference Frequency” is the reference frequency detected internally, which transitions the PLL into self clocked mode.
4 Self clocked mode frequency is the frequency that the PLL operates at when the reference frequency falls below f_{LOR} with default MFD/RFD settings.
5 This parameter is guaranteed by characterization before qualification rather than 100% tested.
6 Proper PC board layout procedures must be followed to achieve specifications.
7 This specification applies to the period required for the PLL to relock after changing the MFD frequency control bits in the synthesizer control register (SYNCR).
8 Assuming a reference is available at power up, lock time is measured from the time V_{DD} and V_{DDSYN} are valid to $\overline{\text{RSTOUT}}$ negating. If the crystal oscillator is being used as the reference for the PLL, then the crystal start up time must be added to the PLL lock time to determine the total start-up time.
9 $t_{lpll} = (64 * 4 * 5 + 5\ \tau)\ T_{ref}$, where $T_{ref} = 1/F_{ref\_crystal} = 1/F_{ref\_ext} = 1/F_{ref\_1:1}$, and $\tau = 1.57x10^{-6}\ 2(MFD + 2)$.
10 PLL is operating in 1:1 PLL mode.
11 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum $f_{sys/2}$. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the PLL circuitry via V_{DDSYN} and V_{SSSYN} and variation in crystal oscillator frequency increase the Cjitter percentage for a given interval.
12 Values are with frequency modulation disabled. If frequency modulation is enabled, jitter is the sum of Cjitter+Cmod.
13 Modulation percentage applies over an interval of 10µs, or equivalently the modulation rate is 100KHz.
14 Modulation rate selected must not result in $f_{sys/2}$ value greater than the $f_{sys/2}$ maximum specified value. Modulation range determined by hardware design.
15 $f_{sys/2} = f_{ico} / (2 * 2^{RFD})$

Timings listed in Table 11 are shown in Figure 7.

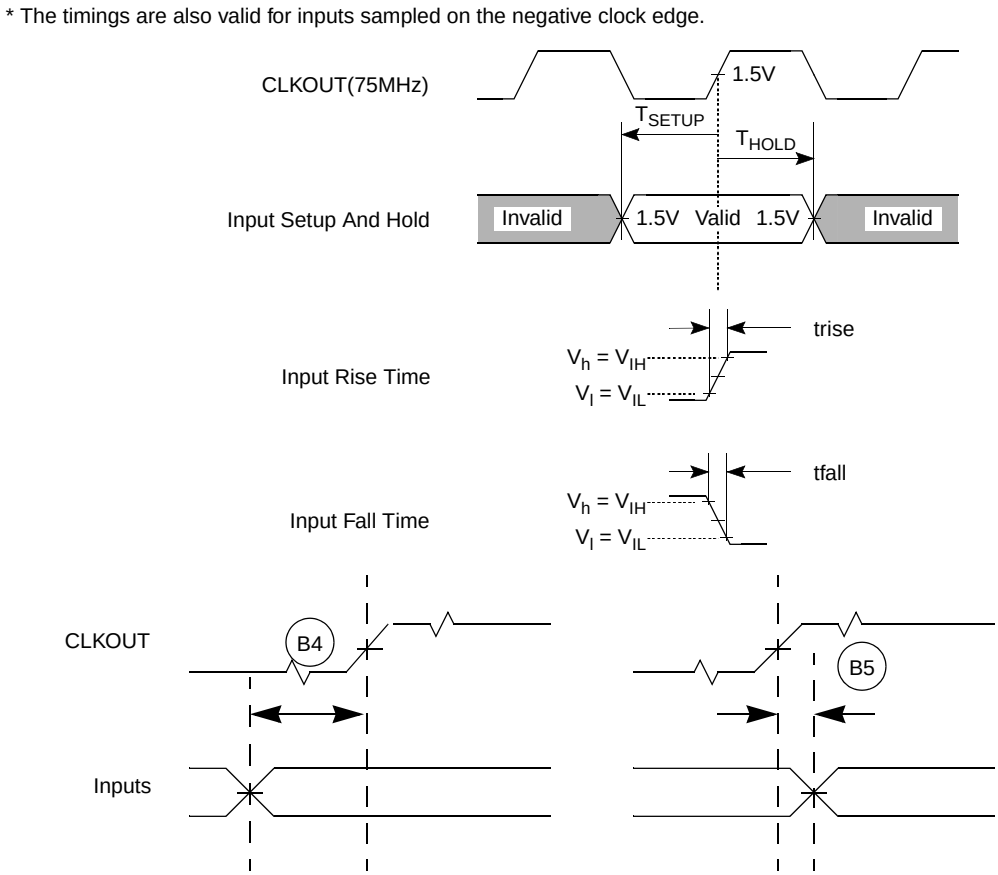


Figure 7. General Input Timing Requirements

7.6 Processor Bus Output Timing Specifications

Table 12 lists processor bus output timings.

Table 12. External Bus Output Timing Specifications

Name	Characteristic	Symbol	Min	Max	Unit
Control Outputs					
B6a	CLKOUT high to chip selects valid [1]	t_{CHCV}	—	$0.5t_{CYC}$ +5	ns
B6b	CLKOUT high to byte enables ($\overline{BS}$[3:0]) valid[2]	t_{CHBV}	—	$0.5t_{CYC}$ +5	ns
B6c	CLKOUT high to output enable ($\overline{OE}$) valid[3]	t_{CHOV}	—	$0.5t_{CYC}$ +5	ns
B7	CLKOUT high to control output ($\overline{BS}$[3:0], $\overline{OE}$) invalid	t_{CHCOI}	$0.5t_{CYC}$+1.5	—	ns
B7a	CLKOUT high to chip selects invalid	t_{CHCI}	$0.5t_{CYC}$+1.5	—	ns

Table 12. External Bus Output Timing Specifications (continued)

Name	Characteristic	Symbol	Min	Max	Unit
Address and Attribute Outputs					
B8	CLKOUT high to address (A[23:0]) and control ($\overline{TS}$, $\overline{TSIZ}$[1:0], $\overline{TIP}$, R/$\overline{W}$) valid	t_{CHAV}	—	9	ns
B9	CLKOUT high to address (A[23:0]) and control ($\overline{TS}$, $\overline{TSIZ}$[1:0], $\overline{TIP}$, R/$\overline{W}$) invalid	t_{CHAI}	1.5	—	ns
Data Outputs					
B11	CLKOUT high to data output (D[31:0]) valid	t_{CHDOV}	—	9	ns
B12	CLKOUT high to data output (D[31:0]) invalid	t_{CHDOI}	1.5	—	ns
B13	CLKOUT high to data output (D[31:0]) high impedance	t_{CHDOZ}	—	9	ns

1 $\overline{CS}$ transitions after the falling edge of CLKOUT.
2 $\overline{BS}$ transitions after the falling edge of CLKOUT.
3 $\overline{OE}$ transitions after the falling edge of CLKOUT.

Figure 9 shows a bus cycle terminated by $\overline{TA}$ showing timings listed in Table 12.

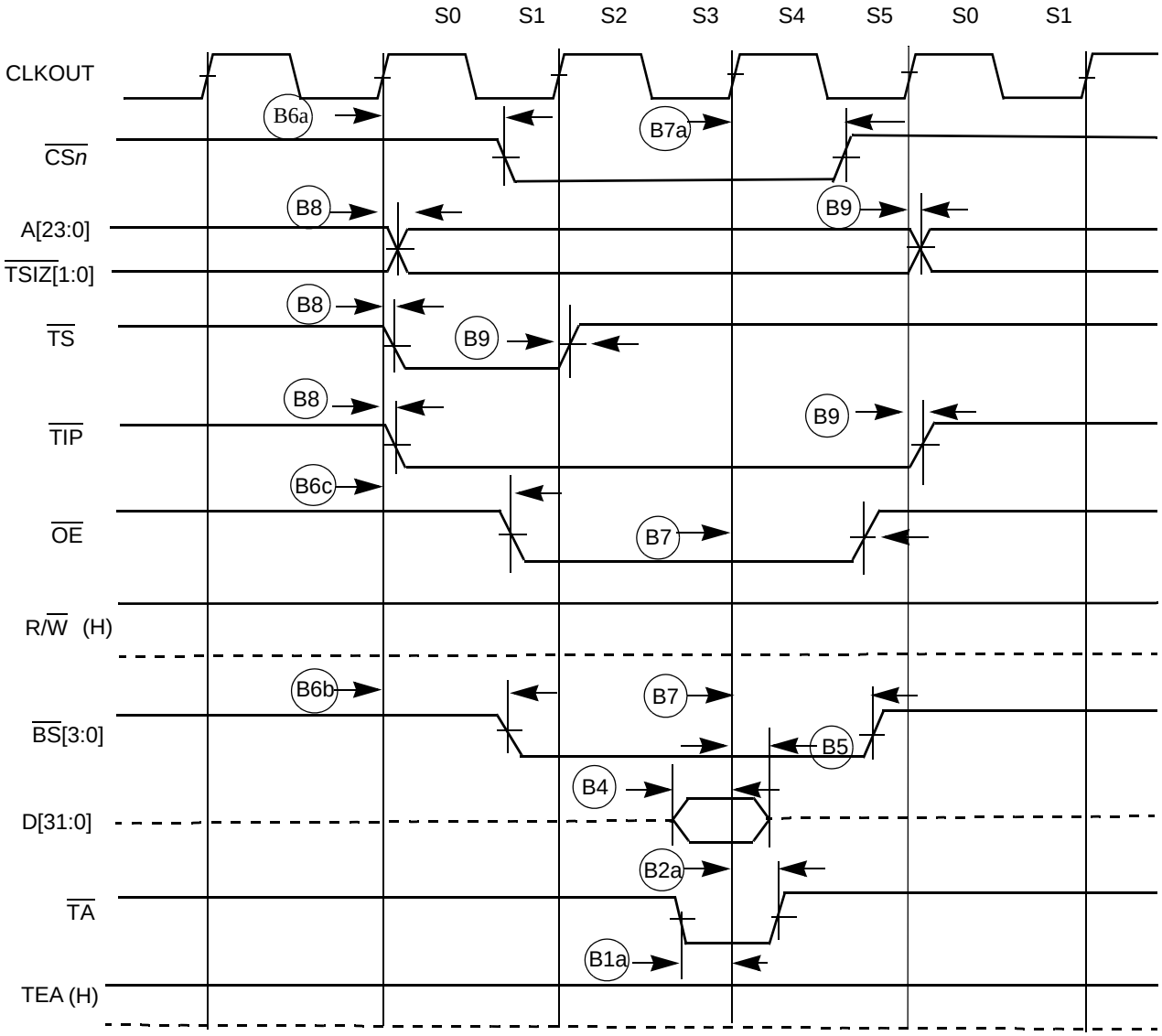


Figure 9. SRAM Read Bus Cycle Terminated by $\overline{TA}$

Figure 10 shows an SRAM bus cycle terminated by $\overline{\text{TEA}}$ showing timings listed in Table 12.

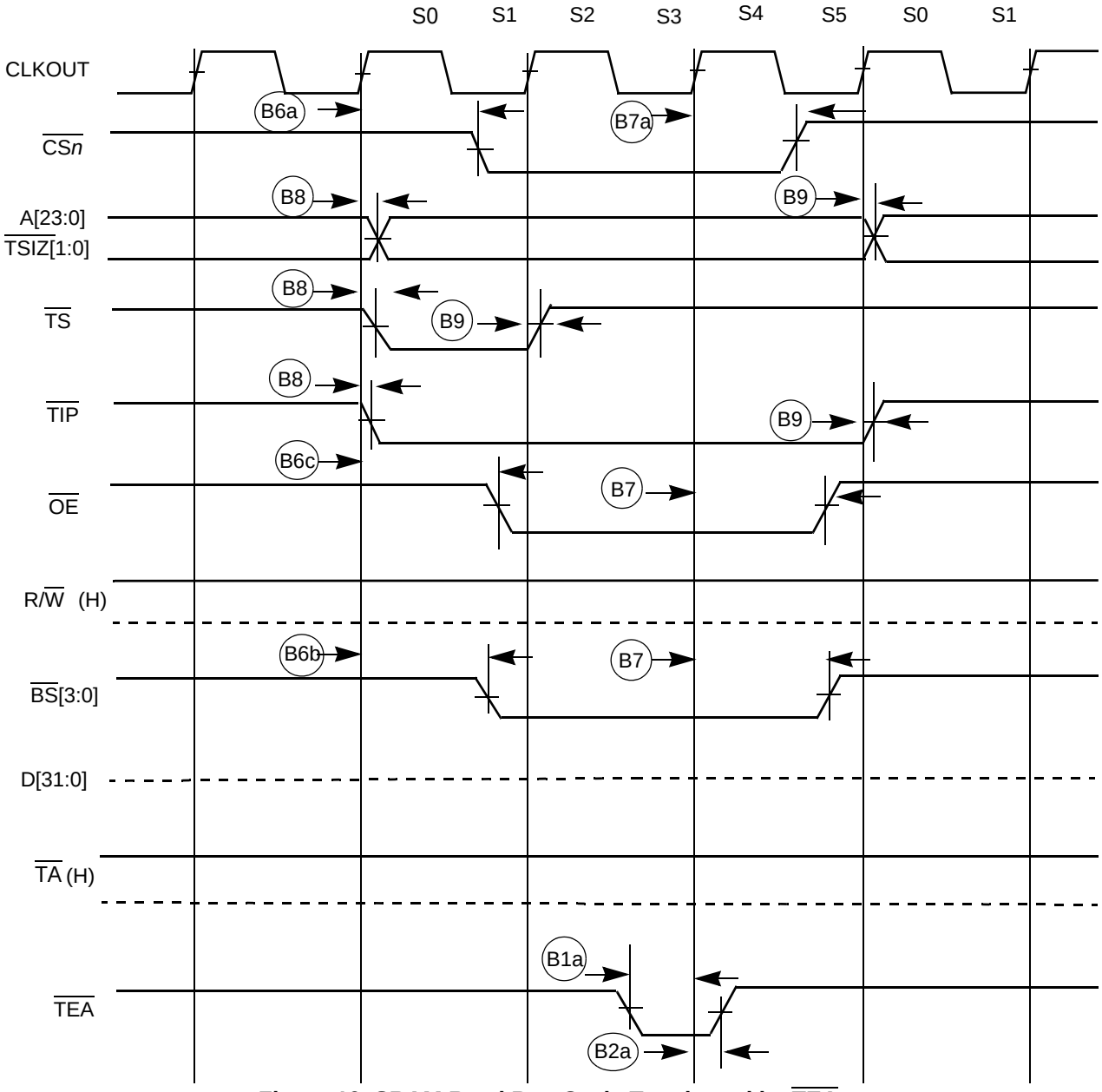
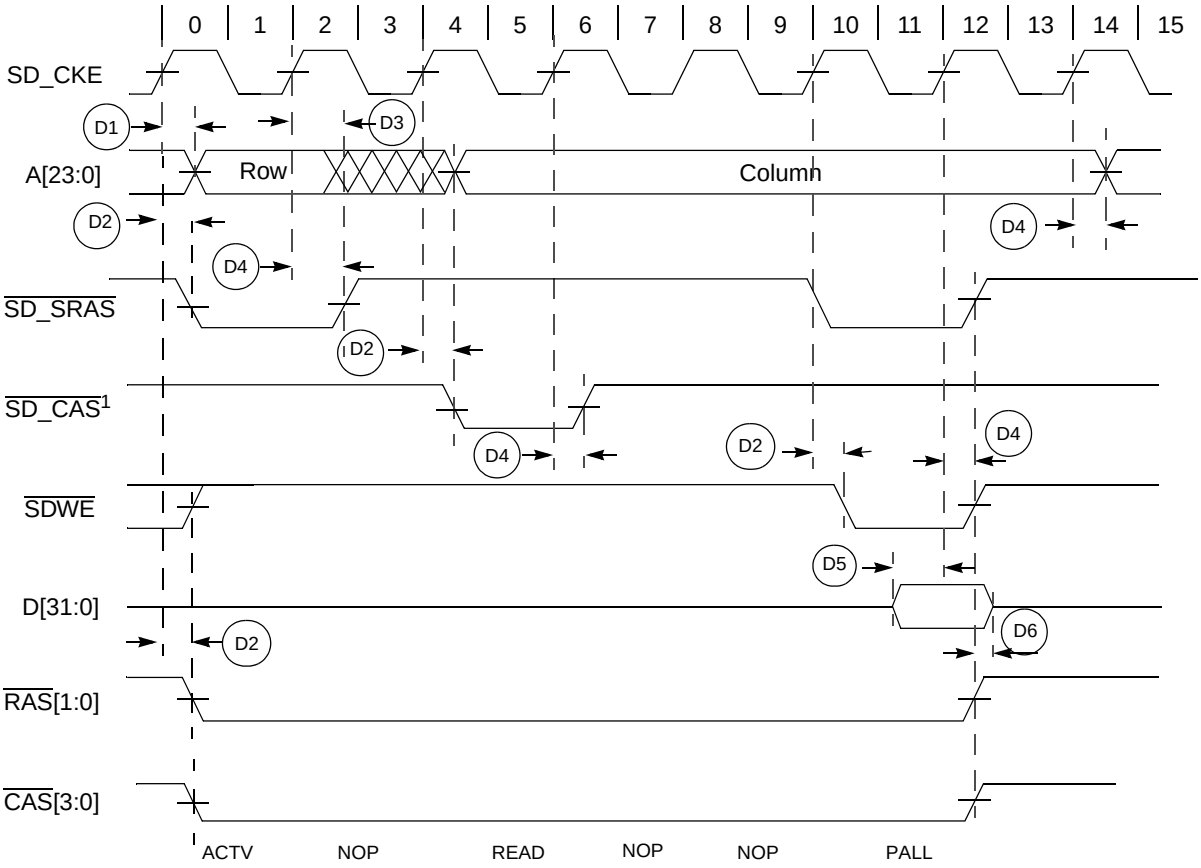


Figure 10. SRAM Read Bus Cycle Terminated by $\overline{\text{TEA}}$

Figure 11 shows an SDRAM read cycle.



1 DACR[CASL] = 2

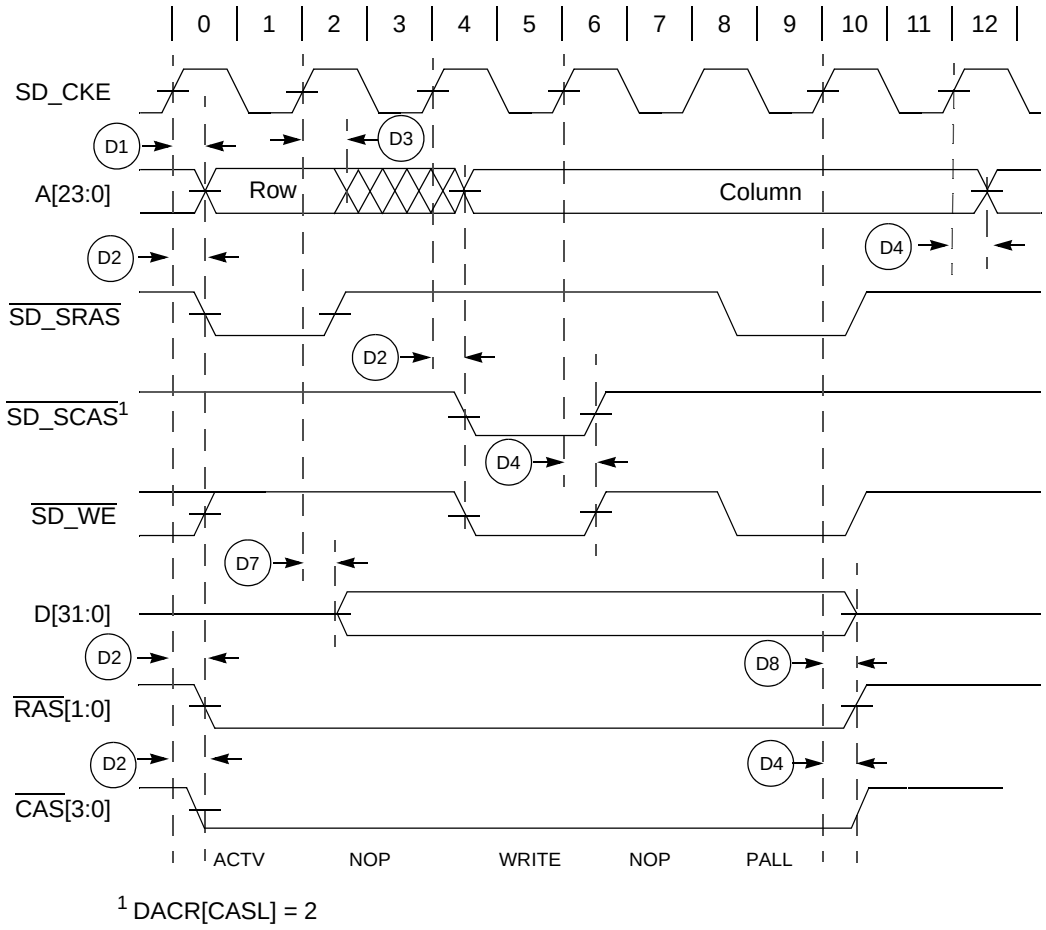
Figure 11. SDRAM Read Cycle

Table 13. SDRAM Timing

NUM	Characteristic	Symbol	Min	Max	Unit
D1	CLKOUT high to SDRAM address valid	t_{CHDAV}	—	9	ns
D2	CLKOUT high to SDRAM control valid	t_{CHDCV}	—	9	ns
D3	CLKOUT high to SDRAM address invalid	t_{CHDAI}	1.5	—	ns
D4	CLKOUT high to SDRAM control invalid	t_{CHDCI}	1.5	—	ns
D5	SDRAM data valid to CLKOUT high	t_{DDVCH}	4	—	ns
D6	CLKOUT high to SDRAM data invalid	t_{CHDDI}	1.5	—	ns
D7[1]	CLKOUT high to SDRAM data valid	t_{CHDDVW}	—	9	ns
D8[1]	CLKOUT high to SDRAM data invalid	t_{CHDDIW}	1.5	—	ns

1 D7 and D8 are for write cycles only.

Figure 12 shows an SDRAM write cycle.



1 DACR[CASL] = 2

Figure 12. SDRAM Write Cycle

7.7 General Purpose I/O Timing

Table 14. GPIO Timing[1]

NUM	Characteristic	Symbol	Min	Max	Unit
G1	CLKOUT High to GPIO Output Valid	t_{CHPOV}	—	10	ns
G2	CLKOUT High to GPIO Output Invalid	t_{CHPOI}	1.5	—	ns
G3	GPIO Input Valid to CLKOUT High	t_{PVCH}	9	—	ns
G4	CLKOUT High to GPIO Input Invalid	t_{CHPI}	1.5	—	ns

1 GPIO pins include: INT, UART, Timer, $\overline{\text{DREQ}n}$ and $\overline{\text{DACK}n}$ pins.

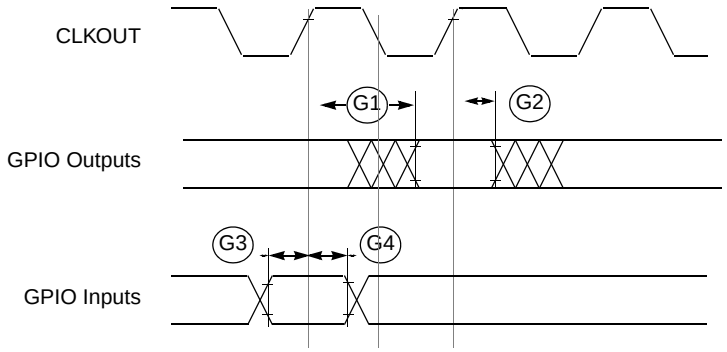


Figure 13. GPIO Timing

7.8 Reset and Configuration Override Timing

Table 15. Reset and Configuration Override Timing
(V_{DD} = 2.7 to 3.6 V, V_{SS} = 0 V, T_A = T_L to T_H)[1]

NUM	Characteristic	Symbol	Min	Max	Unit
R1	$\overline{\text{RESET}}$ Input valid to CLKOUT High	t_{RVCH}	9	—	ns
R2	CLKOUT High to $\overline{\text{RESET}}$ Input invalid	t_{CHRI}	1.5	—	ns
R3	$\overline{\text{RESET}}$ Input valid Time [2]	t_{RIVT}	5	—	t_{CYC}
R4	CLKOUT High to $\overline{\text{RSTOUT}}$ Valid	t_{CHROV}	—	10	ns
R5	$\overline{\text{RSTOUT}}$ valid to Config. Overrides valid	t_{ROVCV}	0	—	ns
R6	Configuration Override Setup Time to $\overline{\text{RSTOUT}}$ invalid	t_{COS}	20	—	t_{CYC}
R7	Configuration Override Hold Time after $\overline{\text{RSTOUT}}$ invalid	t_{COH}	0	—	ns
R8	$\overline{\text{RSTOUT}}$ invalid to Configuration Override High Impedance	t_{ROICZ}	—	1	t_{CYC}

1 All AC timing is shown with respect to 50% V_{DD} levels unless otherwise noted.
2 During low power STOP, the synchronizers for the $\overline{\text{RESET}}$ input are bypassed and $\overline{\text{RESET}}$ is asserted asynchronously to the system. Thus, $\overline{\text{RESET}}$ must be held a minimum of 100 ns.

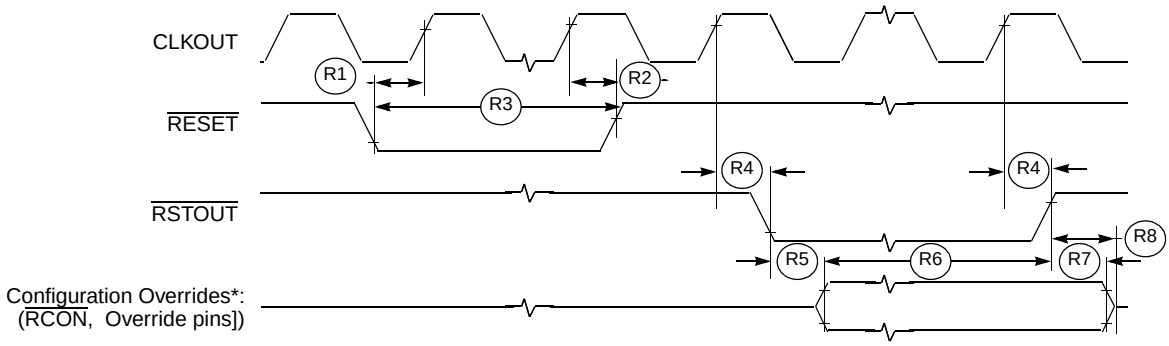


Figure 14. $\overline{\text{RESET}}$ and Configuration Override Timing

Refer to the chip configuration module (CCM) chapter in the device's reference manual for more information.

7.10.2 MII Transmit Signal Timing (ETXD[3:0], ETXEN, ETXER, ETXCLK)

Table 19 lists MII transmit channel timings.

The transmitter functions correctly up to a ETXCLK maximum frequency of 25 MHz +1%. The processor clock frequency must exceed twice the ETXCLK frequency.

Table 19. MII Transmit Signal Timing

Num	Characteristic	Min	Max	Unit
M5	ETXCLK to ETXD[3:0], ETXEN, ETXER invalid	5	—	ns
M6	ETXCLK to ETXD[3:0], ETXEN, ETXER valid	—	25	ns
M7	ETXCLK pulse width high	35%	65%	ETXCLK period
M8	ETXCLK pulse width low	35%	65%	ETXCLK period

Figure 17 shows MII transmit signal timings listed in Table 19.

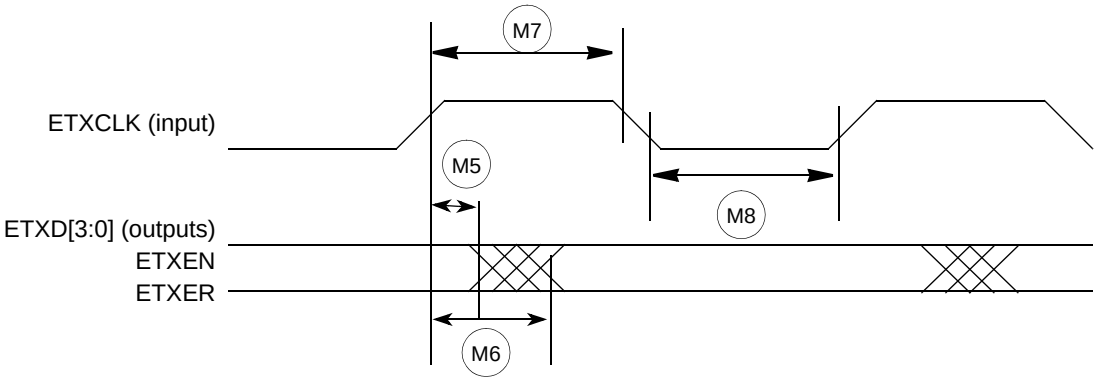


Figure 17. MII Transmit Signal Timing Diagram

7.10.3 MII Async Inputs Signal Timing (ECRS and ECOL)

Table 20 lists MII asynchronous inputs signal timing.

Table 20. MII Async Inputs Signal Timing

Num	Characteristic	Min	Max	Unit
M9	ECRS, ECOL minimum pulse width	1.5	—	ETXCLK period

Figure 18 shows MII asynchronous input timings listed in Table 20.

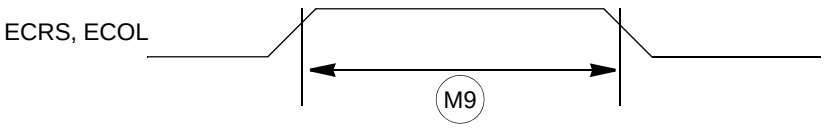


Figure 18. MII Async Inputs Timing Diagram

7.10.4 MII Serial Management Channel Timing (EMDIO and EMDC)

Table 21 lists MII serial management channel timings. The FEC functions correctly with a maximum MDC frequency of 2.5 MHz.

Table 21. MII Serial Management Channel Timing

Num	Characteristic	Min	Max	Unit
M10	EMDC falling edge to EMDIO output invalid (minimum propagation delay)	0	—	ns
M11	EMDC falling edge to EMDIO output valid (max prop delay)	—	25	ns
M12	EMDIO (input) to EMDC rising edge setup	10	—	ns
M13	EMDIO (input) to EMDC rising edge hold	0	—	ns
M14	EMDC pulse width high	40%	60%	MDC period
M15	EMDC pulse width low	40%	60%	MDC period

Figure 19 shows MII serial management channel timings listed in Table 21.

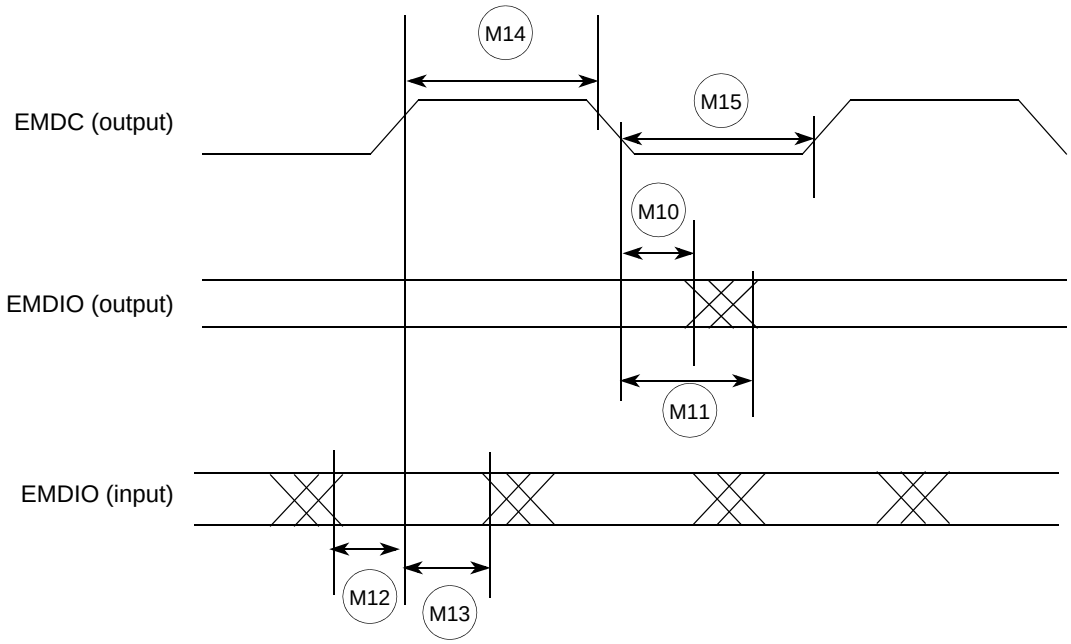


Figure 19. MII Serial Management Channel Timing Diagram

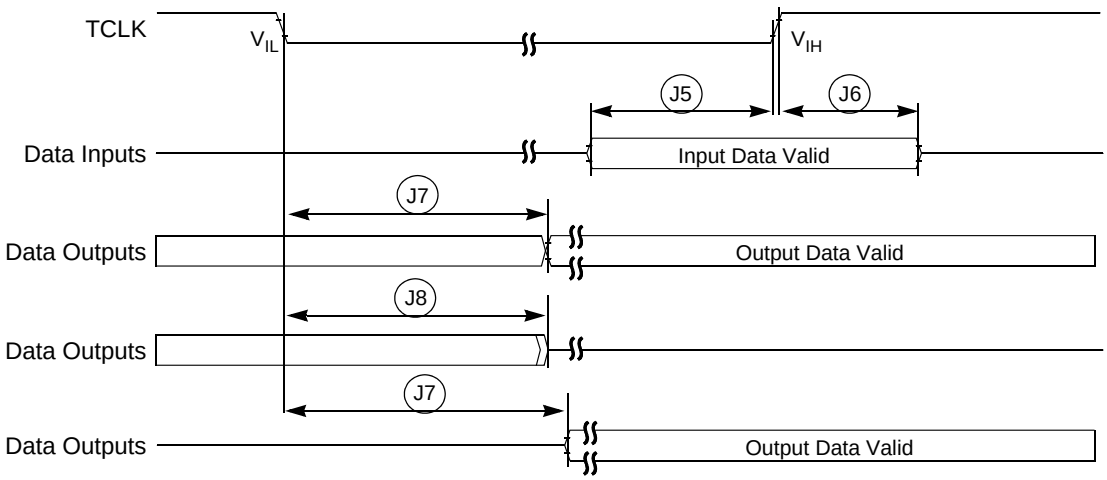


Figure 22. Boundary Scan (JTAG) Timing

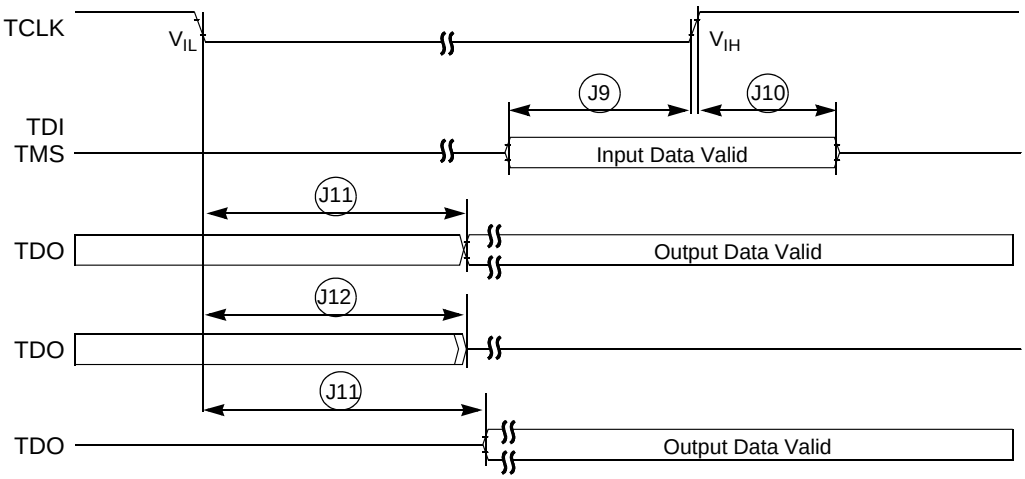


Figure 23. Test Access Port Timing

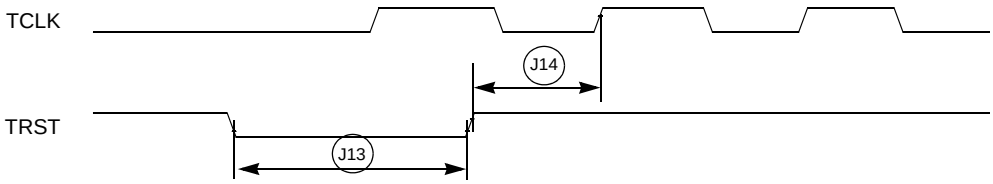


Figure 24. $\overline{\text{TRST}}$ Timing